Shizuo Fujita

List of Publications by Citations

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137 papers	5,301 citations	36 h-index	70 g-index
142 ext. papers	5,875 ext. citations	2 avg, IF	5.93 L-index

#	Paper	IF	Citations
137	Role of self-formed InGaN quantum dots for exciton localization in the purple laser diode emitting at 420 nm. *Applied Physics Letters*, **1997**, 70, 981-983	3.4	835
136	Ga2O3Thin Film Growth onc-Plane Sapphire Substrates by Molecular Beam Epitaxy for Deep-Ultraviolet Photodetectors. *Japanese Journal of Applied Physics*, **2007**, 46, 7217-7220	1.4	399
135	Heteroepitaxy of Corundum-Structured Ga2O3Thin Films on Al2O3Substrates by Ultrasonic Mist Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2008**, 47, 7311-7313	1.4	295
134	Vertical Solar-Blind Deep-Ultraviolet Schottky Photodetectors Based on Ga2O3Substrates. *Applied Physics Express*, **2008**, 1, 011202	2.4	270
133	Wide-bandgap semiconductor materials: For their full bloom. *Japanese Journal of Applied Physics*, **2015**, 54, 030101	1.4	201
132	Molecular Beam Epitaxy of High Magnesium Content Single-Phase Wurzite MgxZn1-xO Alloys ($xsimeq 0.5$) and Their Application to Solar-Blind Region Photodetectors. *Japanese Journal of Applied Physics*, **2003**, 42, L401-L403	1.4	152
131	Self-organized ZnO quantum dots on SiO2/Si substrates by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2002**, 81, 5036-5038	3.4	135
130	Surface morphology of homoepitaxial Ga2O3 thin films grown by molecular beam epitaxy. *Thin Solid Films*, **2008**, 516, 5768-5771	2.2	112
129	Flame Detection by a Ga2O3-Based Sensor. *Japanese Journal of Applied Physics*, **2009**, 48, 011605	1.4	111
128	Epitaxial growth of corundum-structured wide band gap III-oxide semiconductor thin films. *Journal of Crystal Growth*, **2014**, 401, 588-592	1.6	102
127	Al2xGa2-2xO3Thin Film Growth by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2009**, 48, 070202	1.4	91
126	Growth of Crystalline Zinc Oxide Thin Films by Fine-Channel-Mist Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2008**, 47, 4669-4675	1.4	89
125	Fabrication of wide-band-gap MgxZn1O quasi-ternary alloys by molecular-beam epitaxy. *Applied Physics Letters*, **2005**, 86, 192911	3.4	85
124	Evolution of corundum-structured III-oxide semiconductors: Growth, properties, and devices. *Japanese Journal of Applied Physics*, **2016**, 55, 1202A3	1.4	81
123	Linear-Source Ultrasonic Spray Chemical Vapor Deposition Method for Fabrication of ZnMgO Films and Ultraviolet Photodetectors. *Japanese Journal of Applied Physics*, **2006**, 45, L857-L859	1.4	77
122	Stimulated emission from optically pumped GaN quantum dots. *Applied Physics Letters*, **1997**, 71, 1299-1301	3.4	74
121	Fabrication of Highly Crystalline Corundum-Structured (Ga1-xFex)2O3Alloy Thin Films on Sapphire Substrates. *Applied Physics Express*, **2009**, 2, 075501	2.4	69

120	Growth Rate Enhancement by Xenon Lamp Irradiation in Organometallic Vapor-Phase Epitaxy of ZnSe. *Japanese Journal of Applied Physics*, **1987**, 26, L2000-L2002	1.4	67
119	Conductivity control of Sn-doped Ga2O3thin films grown on sapphire substrates. *Japanese Journal of Applied Physics*, **2016**, 55, 1202BA	1.4	63
118	Properties of Ga2O3-based (Inx Ga1)2O3 alloy thin films grown by molecular beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 3113-3115		60
117	Low-Temperature Growth of ZnO Thin Films by Linear Source Ultrasonic Spray Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2007**, 46, 6811-6813	1.4	60
116	Growth of corundum-structured In2O3 thin films on sapphire substrates with Fe2O3 buffer layers. *Journal of Crystal Growth*, **2013**, 364, 30-33	1.6	55
115	Self-organized CdSe quantum dots onto cleaved GaAs (110) originating from StranskiKrastanow growth mode. *Applied Physics Letters*, **1997**, 70, 3278-3280	3.4	54
114	Band gap and function engineering for novel functional alloy semiconductors: Bloomed as magnetic properties at room temperature with (GaFe)2O3. *Journal of Applied Physics*, **2013**, 113, 233901	2.5	53
113	Homoepitaxial growth of beta gallium oxide films by mist chemical vapor deposition. *Japanese Journal of Applied Physics*, **2016**, 55, 1202B8	1.4	51
112	A power device material of corundum-structured Ga2O3fabricated by MIST EPITAXY technique. *Japanese Journal of Applied Physics*, **2018**, 57, 02CB18	1.4	50
111	Growth characteristics of corundum-structured (Al Ga1)2O3/Ga2O3 heterostructures on sapphire substrates. *Journal of Crystal Growth*, **2016**, 436, 150-154	1.6	50
110	Metalorganic Molecular Beam Epitaxial Growth of ZnSe and ZnS on GaAs Substrates Pretreated with (NH4)2SxSolution. *Japanese Journal of Applied Physics*, **1990**, 29, L144-L147	1.4	50
109	Reduction in edge dislocation density in corundum-structured Ga2O3layers on sapphire substrates with quasi-graded (Al,Ga)2O3buffer layers. *Applied Physics Express*, **2016**, 9, 071101	2.4	49
108	Electrical properties of r2O3/Ga2O3 pn heterojunction diode and band alignment of the heterostructure. *Applied Physics Letters*, **2018**, 113, 212104	3.4	49
107	Thermal stability of single crystalline alpha gallium oxide films on sapphire substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1592-1595		47
106	Effects of annealing atmosphere and temperature on acceptor activation in ZnSe:N grown by photoassisted MOVPE. *Journal of Crystal Growth*, **1996**, 159, 312-316	1.6	46
105	Optically Pumped Blue-Green Laser Operation Above Room-Temperature in Zn0.80Cd0.20Se-ZnS0.08Se0.92Multiple Quantum Well Structures Grown by Metalorganic Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **1991**, 30, L605-L607	1.4	43
104	Epitaxial ZnO Thin Films ona-Plane Sapphire Substrates Grown by Ultrasonic Spray-Assisted Mist Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2009**, 48, 121103	1.4	41
103	Transparent conductive zinc-oxide-based films grown at low temperature by mist chemical vapor deposition. *Thin Solid Films*, **2015**, 597, 30-38	2.2	37

102	Rheed and x-ray characterization of InGaAs/GaAs grown by MBE. *Journal of Crystal Growth*, **1989**, 95, 224-227	1.6	36
101	Growth of SnO2 crystalline thin films by mist chemical vapour deposition method. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 540-542		35
100	Selective formation of ZnO nanodots on nanopatterned substrates by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2003**, 83, 3593-3595	3.4	35
99	Enhanced thermal stability of alpha gallium oxide films supported by aluminum doping. *Japanese Journal of Applied Physics*, **2015**, 54, 030301	1.4	33
98	A Defect Model for Photoirradiated Semiconductors Suppression of the Self-Compensation in II-VI Materials *Japanese Journal of Applied Physics*, **1991**, 30, 3475-3481	1.4	31
97	Growth of corundum-structured (InxGa1)2O3 alloy thin films on sapphire substrates with buffer layers. *Journal of Crystal Growth*, **2014**, 401, 670-672	1.6	30
96	Growth and Band Gap Control of Corundum-Structured $alpha$-(AlGa)$_{2}$O$_{3}$ Thin Films on Sapphire by Spray-Assisted Mist Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2012**, 51, 100207	1.4	30
95	Evaluation of band alignment of Ga2O3/(AlxGa1)2O3heterostructures by X-ray photoelectron spectroscopy. *Japanese Journal of Applied Physics*, **2018**, 57, 040314	1.4	29
94	Growth characteristics of single-crystalline ZnMgO layers by ultrasonic spray assisted mist CVD technique. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 1460-1463	1.3	28
93	Control of Crystal Structure of Ga2O3 on Sapphire Substrate by Introduction of (AlxGa1)2O3 Buffer Layer. *Physica Status Solidi (B): Basic Research*, **2018**, 255, 1700326	1.3	27
92	Corundum-structured phase Ga2O3-Cr2O3-Fe2O3 alloy system for novel functions. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2467-2470		27
91	An approach for single crystalline zinc oxide thin films with fine channel mist chemical vapor deposition method. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 3138-3140		27
90	Fabrication and Properties of ZnO Thin Films Prepared by Fine Channel Mist Mehtod. *Zairyo/Journal of the Society of Materials Science, Japan*, **2006**, 55, 153-158	0.1	27
89	Formation of Semi-Insulating Layers on Semiconducting Ga2O3Single Crystals by Thermal Oxidation. *Japanese Journal of Applied Physics*, **2013**, 52, 051101	1.4	25
88	Analysis of Hump Characteristics in Thin-Film Transistors With ZnO Channels Deposited by Sputtering at Various Oxygen Partial Pressures. *IEEE Electron Device Letters*, **2010**,	4.4	25
87	Electrical characterization of Si-doped n-type Ga2O3 on sapphire substrates. *MRS Advances*, **2018**, 3, 171-177	0.7	24
86	Step-flow growth of homoepitaxial ZnO thin films by ultrasonic spray-assisted MOVPE. *Journal of Crystal Growth*, **2008**, 310, 5007-5010	1.6	22
85	Organometallic vapor-phase epitaxial growth of cubic ZnCdS lattice-matched to GaAs substrate. *Journal of Crystal Growth*, **1990**, 99, 437-440	1.6	22

84	Fabrication of PEDOT:PSS/ZnMgO Schottky-type ultraviolet sensors on glass substrates with solution-based mist deposition technique and hard-mask patterning. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 613-615		21
83	Photoassisted Metalorganic Vapor-Phase Epitaxy of Nitrogen-Doped ZnSe Using Tertiarybutylamine as Doping Source. *Japanese Journal of Applied Physics*, **1993**, 32, L1153-L1156	1.4	21
82	Silver oxide Schottky contacts and metal semiconductor field-effect transistors on SnO2thin films. *Applied Physics Express*, **2016**, 9, 041101	2.4	21
81	Extraction of Trap Densities in ZnO Thin-Film Transistors and Dependence on Oxygen Partial Pressure During Sputtering of ZnO Films. *IEEE Transactions on Electron Devices*, **2011**, 58, 3018-3024	2.9	20
80	Surface termination structure of □Ga2O3 film grown by mist chemical vapor deposition. *Applied Physics Letters*, **2016**, 108, 251602	3.4	20
79	Tin oxide coating by nonvacuum-based mist chemical vapor deposition on stainless steel separators for polymer electrolyte fuel cells. *Japanese Journal of Applied Physics*, **2018**, 57, 117103	1.4	20
78	Ultrasonic-assisted mist chemical vapor deposition of II-oxide and related oxide compounds. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 1225-1228		19
77	Relation between GaAs surface morphology and incorporation of hexagonal GaN into cubic GaN. *Journal of Crystal Growth*, **1999**, 196, 41-46	1.6	18
76	Oriented growth of beta gallium oxide thin films on yttrium-stabilized zirconia substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1596-1599		17
75	Enhancement of epitaxial lateral overgrowth in the mist chemical vapor deposition of □Ga2O3 by using a-plane sapphire substrate. *Japanese Journal of Applied Physics*, **2019**, 58, 120912	1.4	16
74	Gas-Source Molecular Beam Epitaxial Growth of (Zn, Mg)(S, Se) Using Bis-methylcyclopentadienyl-magnesium and Hydrogen Sulfide. *Japanese Journal of Applied Physics*, **1994**, 33, L290-L293	1.4	16
73	Growth of rocksalt-structured MgxZn1□O (x> 0.5) films on MgO substrates and their deep-ultraviolet luminescence. *Applied Physics Express*, **2016**, 9, 111102	2.4	15
72	Mist chemical vapor deposition of aluminum oxide thin films for rear surface passivation of crystalline silicon solar cells. *Applied Physics Express*, **2014**, 7, 021303	2.4	15
71	Thermal annealing effects on p-type conductivity of nitrogendoped ZnSe grown by metalorganic vapor phase epitaxy. *Journal of Electronic Materials*, **1995**, 24, 137-141	1.9	15
70	Photo-assisted metalorganic vapor-phase epitaxy for nitrogen doping and fabrication of blue-green light emitting devices of ZnSe-based semiconductors. *Journal of Crystal Growth*, **1994**, 138, 737-744	1.6	15
69	Metalorganic vapor-phase epitaxy of p-type ZnSe and p/n junction diodes. *Journal of Crystal Growth* , **1994**, 145, 552-556	1.6	15
68	Evaluation of Misfit Relaxation in □Ga2O3Epitaxial Growth on □Al2O3Substrate. *Japanese Journal of Applied Physics*, **2012**, 51, 020201	1.4	15
67	Electrical Conductive Corundum-Structured □Ga2O3Thin Films on Sapphire with Tin-Doping Grown by Spray-Assisted Mist Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2012**, 51, 070203	1.4	15

66	Growth and metal□oxide□semiconductor field-effect transistors of corundum-structured alpha indium oxide semiconductors. *Applied Physics Express*, **2015**, 8, 095503	2.4	14
65	Integration of GaN with Si using a AuGe-mediated wafer bonding technique. *Applied Physics Letters*, **2000**, 77, 3959-3961	3.4	14
64	Ultra-wide bandgap corundum-structured p-type □(Ir,Ga)2O3 alloys for □Ga2O3 electronics. *Applied Physics Letters*, **2021**, 118, 102104	3.4	14
63	Tunable band offsets in ZnSe/GaAs heterovalent heterostructures grown by metalorganic vapor phase epitaxy. *Journal of Applied Physics*, **1997**, 82, 2984-2989	2.5	13
62	Mechanism analysis of photoleakage current in ZnO thin-film transistors using device simulation. *Applied Physics Letters*, **2010**, 97, 163503	3.4	12
61	Effects of chemical stoichiometry of channel region on bias instability in ZnO thin-film transistors. *Applied Physics Letters*, **2011**, 98, 103512	3.4	12
60	Photoassisted growth of II□VI semiconductor films. *Applied Surface Science*, **1995**, 86, 431-436	6.7	11
59	Pure deep-ultraviolet cathodoluminescence from rocksalt-structured MgZnO grown with carbon-free precursors. *Applied Physics Express*, **2019**, 12, 052011	2.4	10
58	Deep-Ultraviolet Luminescence of Rocksalt-Structured MgxZn1□xO (x > 0.5) Films on MgO Substrates. *Journal of Electronic Materials*, **2018**, 47, 4356-4360	1.9	10
57	Growth of p-type Zn(S)Se layers by MOVPE. *Journal of Crystal Growth*, **1998**, 184-185, 398-405	1.6	10
56	MO(GS)MBE and photo-MO(GS)MBE of II□VI semiconductors. *Journal of Crystal Growth*, **1996**, 164, 196-201	1.6	10
55	Fabrication of II□VI semiconductor quantum well structures in ZnCdSSe alloy systems. *Physica B: Condensed Matter*, **1993**, 191, 57-70	2.8	9
54	Formation of aluminum tris (8-hydroxyquinoline) solution in methanol and fabrication of thin films by ultrasonic spray-assisted vapor deposition. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 1298-1301	1.6	8
53	Thermal stability of □Ga2O3 films grown on c-plane sapphire substrates via mist-CVD. *AIP Advances*, **2020**, 10, 115013	1.5	8
52	Prospects for phase engineering of semi-stable Ga2O3 semiconductor thin films using mist chemical vapor deposition. *Journal of Applied Physics*, **2022**, 131, 090902	2.5	8
51	Single-phase hexagonal GaN grown on AlAs/GaAs(001). *Applied Physics Letters*, **2000**, 77, 244-246	3.4	7
50	Photocatalytic surface reactions in metalorganic vapor-phase epitaxy. *Applied Surface Science*, **1994**, 79-80, 41-46	6.7	7
49	Reduction of Photo-Leakage Current in ZnO Thin-Film Transistors With Dual-Gate Structure. *IEEE Electron Device Letters*, **2011**, 32, 509-511	4.4	6

48	Hexagonal GaN grown on GaAs{11n} substrates by metalorganic vapor-phase epitaxy using AlAs intermediate layers. *Applied Physics Letters*, **2001**, 79, 4133-4135	3.4	6
47	Thermal stability of □(Al x Ga1□)2O3 films grown on c-plane sapphire substrates with an Al composition up to 90%. *Japanese Journal of Applied Physics*, **2021**, 60, SBBD13	1.4	6
46	Corundum-Structured □In2O3 as a Wide-Bandgap Semiconductor for Electrical Devices. *MRS Advances*, **2017**, 2, 301-307	0.7	5
45	Deep states in nitrogen-doped p-ZnSe. *Journal of Applied Physics*, **1998**, 83, 2563-2567	2.5	5
44	Tunable band offsets via control of interface atomic configuration in GaAs-on-ZnSe(001) heterovalent heterostructures. *Journal of Applied Physics*, **1999**, 85, 1514-1519	2.5	5
43	Effects of GaAs buffer layer and lattice-matching on deep levels in Zn(S)Se/GaAs heterostructures. *Journal of Electronic Materials*, **1996**, 25, 217-222	1.9	5
42	Metalorganic vapor phase epitaxy growth and nitrogen-doping of ZnxCd1-xS using photo-assistance. *Journal of Crystal Growth*, **1994**, 145, 570-575	1.6	5
41	69.1: Photo-Leakage Current in ZnO TFTs for Transparent Electronics. *Digest of Technical Papers SID International Symposium*, **2010**, 41, 1029	0.5	4
40	Growth of P-type Znse by metalorganic molecular beam epitaxy using metal Zn and dimethylselenide. *Journal of Electronic Materials*, **1996**, 25, 223-227	1.9	4
39	Ultrasonic Spray-Assisted Solution-Based Vapor-Deposition of Aluminum Tris(8-hydroxyquinoline) Thin Films. *Japanese Journal of Applied Physics*, **2011**, 50, 020204	1.4	4
38	Impact of hydrochloric acid on the epitaxial growth of In2O3 films on (0001)□Al2O3 substrates by mist CVD. *Applied Physics Express*, **2020**, 13, 075504	2.4	3
37	Vertical Schottky barrier diodes of □Ga2O3 fabricated by mist epitaxy **2015**,		3
36	Crystal Structure of Non-Doped and Sn-Doped □(GaFe)2O3 Thin Films.. *Materials Research Society Symposia Proceedings*, **2013**, 1494, 147-152		3
35	Mist deposition technique as a green chemical route for synthesizing oxide and organic thin films. *Materials Research Society Symposia Proceedings*, **2009**, 1220, 4061		3
34	Six-bilayer periodic structures in GaN grown on GaAs(001). *Applied Physics Letters*, **2000**, 76, 330-332	3.4	3
33	Growth of ZnSe/ZnMgSSe quantum well structures by metalorganic molecular beam epitaxy under in situ observation of reflection high energy electron diffraction intensity oscillation. *Journal of Crystal Growth*, **1995**, 150, 738-742	1.6	3
32	Analysis of Deep Traps in Mist Chemical Vapor Deposition-Grown n-Type □Ga2O3 by Photocapacitance Method. *Physica Status Solidi (B): Basic Research*, **2021**, 258, 2000622	1.3	3
31	Thin Film Formation of Transparent Conductive Oxides by Solution-Based Mist Deposition Method toward Hybrid Device Applications. *Materials Research Society Symposia Proceedings*, **2012**, 1400, 1		2

30	Fabrication of Organic Polymer Solar Cells by a Novel Solution-Based Vapor-like Mist Deposition Method. *Materials Research Society Symposia Proceedings*, **2012**, 1390, 47		2
29	A comparative study on deep levels in p-ZnSe grown by MBE, MOMBE and MOVPE. *Journal of Crystal Growth*, **1998**, 184-185, 495-499	1.6	2
28	The mechanism of radiative recombination in light-emitting devices composed on InGaN quantum wells. *Electronics and Communications in Japan*, **1998**, 81, 45-56		2
27	Nucleation processes during metalorganic vapor phase epitaxy of ZnSe on GaAs(001). *Journal of Applied Physics*, **1998**, 84, 1383-1388	2.5	2
26	Electrical Characterization of Movpe-Grown p-Type GaN:Mg Against Annealing Temperature. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1		2
25	Novel p-type oxides with corundum structure for gallium oxide electronics. *Journal of Materials Research*, **2022**, 37, 651-659	2.5	2
24	Corundum-strructured □Ga2O3-based alloys for future power device applications **2017**,		1
23	Fabrication of Corundum-Structured □(InFe)2O3 Alloy Films on Sapphire Substrates by Inserting □Fe2O3 Buffer Layer. *Materials Research Society Symposia Proceedings*, **2013**, 1494, 221-225		1
22	Electrical Characterization of MOVPE-Grown P-Type GaN:Mg Against Annealing Temperature. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 665-670		1
21	Characterization of band offset in □(AlxGa1-x)2O3/ □Ga2O3 heterostructures **2016**,		1
20	Identification of free and bound exciton emission of MgO single crystal in vacuum ultraviolet spectral range. *Applied Physics Letters*, **2021**, 119, 132105	3.4	1
19	Mist Chemical Vapor Deposition Growth of □In2O3 Films Using Indium Oxide Powder as Source Precursor. *Physica Status Solidi (B): Basic Research*,2100414	1.3	0
18	Aluminum Oxide Passivation Layer for Crystalline Silicon Solar Cells Deposited by Mist CVD in Open-Air Atmosphere. *Materials Research Society Symposia Proceedings*, **2014**, 1647, 1		
17	Fundamental Properties and Optical Device Applications of ZnO. *The Review of Laser Engineering*, **2011**, 39, 165-170	0	
16	Artificial Surface Control of Gallium Oxide Semiconductors and Growth of High Quality Single-crystalline Thin Films. *Hyomen Kagaku*, **2010**, 31, 643-650		
15	Fabrication of Organic Small Molecular Thin Films based on Ultrasonic Spray-Assisted Vapor-Deposition Method. *Materials Research Society Symposia Proceedings*, **2012**, 1400, 29		
14	Effect of cleaving environment on the growth of ZnSe on the GaAs (1 1 0) surface by molecular beam epitaxy. *Journal of Materials Science Letters*, **1997**, 16, 1187-1190		
13	Effect of cleaving environment on the growth of ZnSe on the GaAs (110) surface by molecular beam epitaxy. *Journal of Materials Science Letters*, **1997**, 16, 1187-1190		

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12	Ultrasonic spray assisted Mist-CVD method for high-quality crystalline and amorphous oxide semiconductors growth. *Materials Research Society Symposia Proceedings*, **2008**, 1113, 1	
11	Direct Fabrication of ZnO Whiskers Bridging Between Micron-gap Electrodes in Aqueous Solution for Highly Gas Sensing. *Materials Research Society Symposia Proceedings*, **2007**, 1035, 1	
10	Optical Absorption in ZnSe-GaAs Heterovalent Quantum Structures. *Materials Research Society Symposia Proceedings*, **1998**, 535, 71	
9	Luminescence Dynamics of Alq3-Based Multilayer Structures in Terms of HOMO and LUMO Energy Discontinuity. *Materials Research Society Symposia Proceedings*, **1999**, 598, 321	
8	Defect States in p-ZnSe:N Grown by MOVPE. *Materials Research Society Symposia Proceedings*, **1996**, 442, 561	
7	Surface Reconstruction and Morphology of Hydrogen Sulfide Treated GaAs (001) Substrate. *Materials Research Society Symposia Proceedings*, **1996**, 448, 15	
6	Emission Mechanism of the InGaN MQW Grown by MOCVD. *Materials Research Society Symposia Proceedings*, **1996**, 449, 665	
5	Vacuum Ultraviolet Emission Properties of Rocksalt-Structured MgZnO Microcrystals Prepared on Quartz Glass Substrates. *Physica Status Solidi (B): Basic Research*,2100354	1.3
4	Research of Semiconductor Materials That Emit in the Vacuum Ultraviolet Region of 200 nm or Less. *Zairyo/Journal of the Society of Materials Science, Japan*, **2021**, 70, 727-731	0.1
3	Vacuum Deposition and Luminescence Dynamics of Organic Thin Film Multi-Structures. *Shinku/Journal of the Vacuum Society of Japan*, **2001**, 44, 948-955	
2	Molecular Beam Epitaxial Growth Behaviors of Zn1-xCdxSe on the GaAs(110) Surface Cleaved in Ultra High Vacuum.. *Shinku/Journal of the Vacuum Society of Japan*, **1997**, 40, 317-320	
1	Crystal Growth and Device Applications of Corundum-Structured Gallium Oxide. *Zairyo/Journal of the Society of Materials Science, Japan*, **2016**, 65, 631-637	0.1